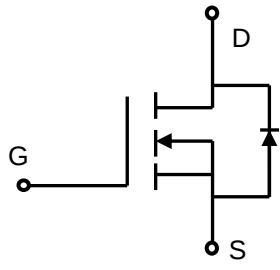


Lonten N-channel 650V, 4A, 930mΩ LonFET™ Power MOSFET

Description LonFET™ Power MOSFET is fabricated using advanced super junction technology. The resulting device has extremely low on resistance, making it especially suitable for applications which require superior power density and outstanding efficiency. Features ♦ Ultra low $R_{DS(on)}$ ♦ Ultra low gate charge (typ. $Q_g = 13.6nC$) ♦ 100% UIS tested ♦ RoHS compliant Applications ♦ Power faction correction (PFC). ♦ Switched mode power supplies (SMPS). ♦ Uninterruptible power supply (UPS).	Product Summary <table> <tr> <td>$V_{DS} @ T_{j,max}$</td><td>700V</td></tr> <tr> <td>$R_{DS(on),max}$</td><td>930mΩ</td></tr> <tr> <td>I_{DM}</td><td>12A</td></tr> <tr> <td>$Q_{g,typ}$</td><td>13.6nC</td></tr> </table>  TO-251  TO-252  TO-220MF  N-Channel MOSFET 	$V_{DS} @ T_{j,max}$	700V	$R_{DS(on),max}$	930mΩ	I_{DM}	12A	$Q_{g,typ}$	13.6nC
$V_{DS} @ T_{j,max}$	700V								
$R_{DS(on),max}$	930mΩ								
I_{DM}	12A								
$Q_{g,typ}$	13.6nC								

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	650	V
Continuous drain current ($T_C = 25^{\circ}C$)	I_D	4	A
($T_C = 100^{\circ}C$)		2.5	A
Pulsed drain current ¹⁾	I_{DM}	12	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ²⁾	E_{AS}	120	mJ
Avalanche energy, repetitive ³⁾	E_{AR}	0.6	mJ
Avalanche current, repetitive ³⁾	I_{AR}	4	A
Power Dissipation TO-220MF ($T_C = 25^{\circ}C$)	P_D	29	W
- Derate above 25°C		0.23	W/°C
Power Dissipation TO-251/ TO-252($T_C = 25^{\circ}C$)		50	W
- Derate above 25°C		0.4	W/°C
Mounting torque To-220MF (M2.5 screws)		50	Ncm
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C
Continuous diode forward current	I_S	4	A
Diode pulse current	$I_{S,pulse}$	12	A

Thermal Characteristics TO-251/TO-252

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$
Soldering temperature, wavesoldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	$^{\circ}\text{C}$

Thermal Characteristics TO-220MF

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.3	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	80	$^{\circ}\text{C/W}$
Soldering temperature, wavesoldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	$^{\circ}\text{C}$

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube	Units/Real
LSD65R930GT	TO-220MF	LSD65R930GT	50	
LSG65R930GT	TO-252	LSG65R930GT		2500
LSH65R930GT	TO-251	LSH65R930GT	72	

Electrical Characteristics

 $T_c = 25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =0.25 mA	650	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =0.25mA	2.5	3.5	4.5	V
Drain cut-off current	I _{DSS}	V _{DS} =650 V, V _{GS} =0 V, T _j = 25°C T _j = 125°C	- -	- 10	1 -	μA
Gate leakage current, Forward	I _{GSSF}	V _{GS} =30 V, V _{DS} =0 V	-	-	50	nA
Gate leakage current, Reverse	I _{GSSR}	V _{GS} =-30 V, V _{DS} =0 V	-	-	-50	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =2A T _j = 25°C T _j = 150°C	- - -	 0.82 1.9	 0.93 -	 Ω
Gate resistance	R _G	f=1 MHz, open drain	-	8	-	Ω
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	-	513	-	pF
Output capacitance	C _{oss}		-	270	-	
Reverse transfer capacitance	C _{rss}		-	4	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 300 V, I _D = 2 A R _G = 12Ω, V _{GS} =10 V	-	18.9	-	ns
Rise time	t _r		-	23	-	
Turn-off delay time	t _{d(off)}		-	43.6	-	
Fall time	t _f		-	11.5	-	
Gate charge characteristics						

Gate to source charge	Q _{gs}	V _{DD} =480 V, I _D =2 A, V _{GS} =0 to 10 V	-	4.1	-	nC
Gate to drain charge	Q _{gd}		-	5.7	-	
Gate charge total	Q _g		-	13.6	-	
	V _{plateau}		-	6	-	V
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =2 A	-	1.0	-	V
Reverse recovery time	t _{rr}	V _R =50 V, I _F =4 A, dI _F /dt=100 A/μs	-	216	-	ns
Reverse recovery charge	Q _{rr}		-	1.4	-	μC
Peak reverse recovery current	I _{rrm}		-	13	-	A

Notes:

1. Limited by maximum junction temperature, maximum duty cycle is 0.75.
2. $I_{AS} = 2\text{ A}$, $V_{DD} = 60\text{ V}$, Starting $T_J = 25^\circ\text{C}$.
3. Repetitive Rating: Pulse width limited by maximum junction temperature.

Electrical Characteristics Diagrams

Figure 1. On-Region Characteristics

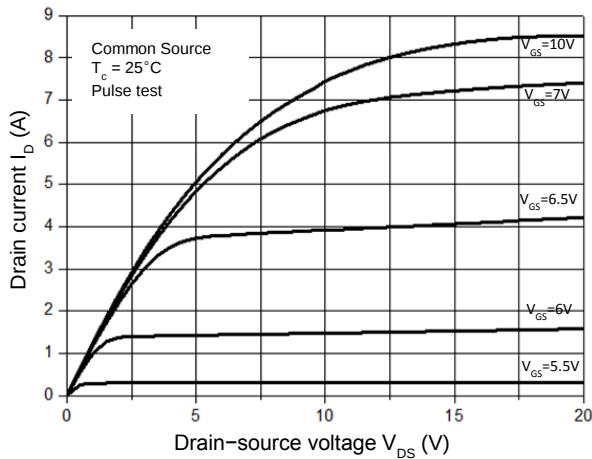


Figure 2. Transfer Characteristics

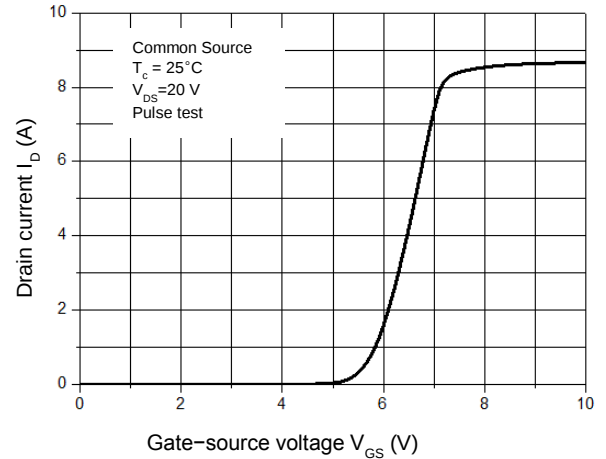


Figure 3. On-Resistance Variation vs. Drain Current

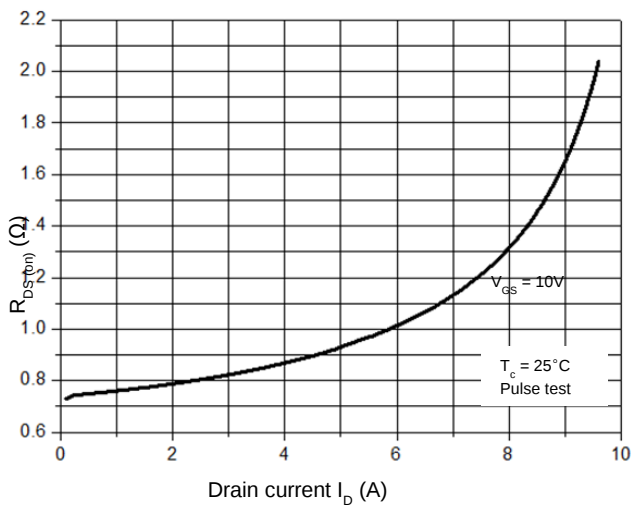


Figure 4. Threshold Voltage vs. Temperature

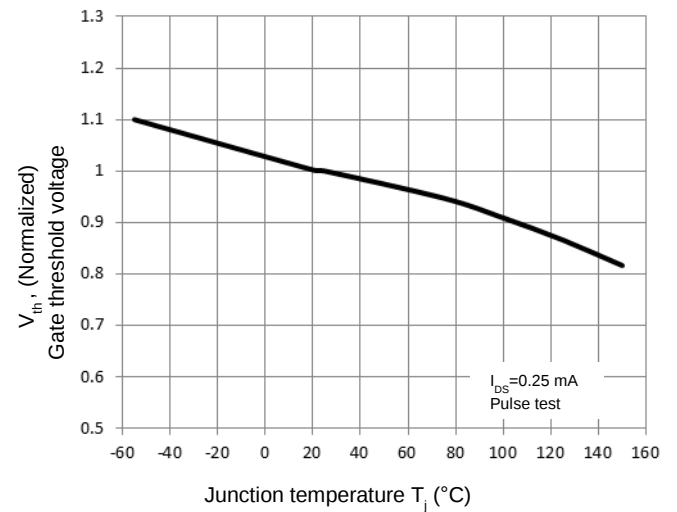


Figure 5. Breakdown Voltage vs. Temperature

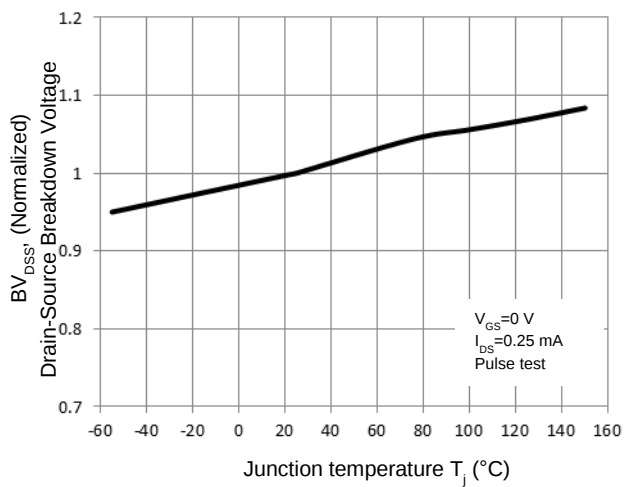


Figure 6. On-Resistance vs. Temperature

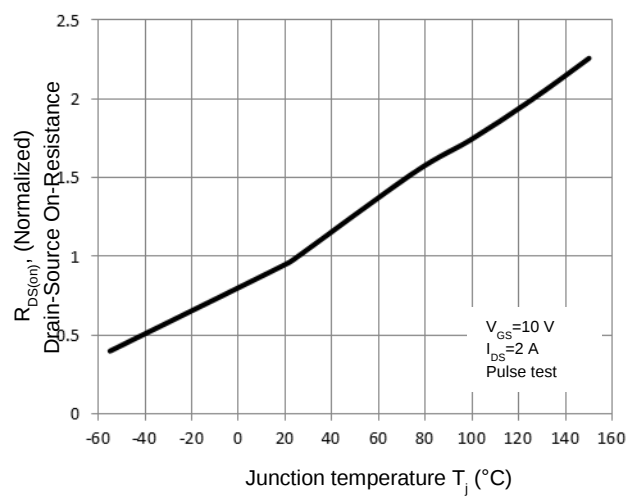


Figure 7. Capacitance Characteristics

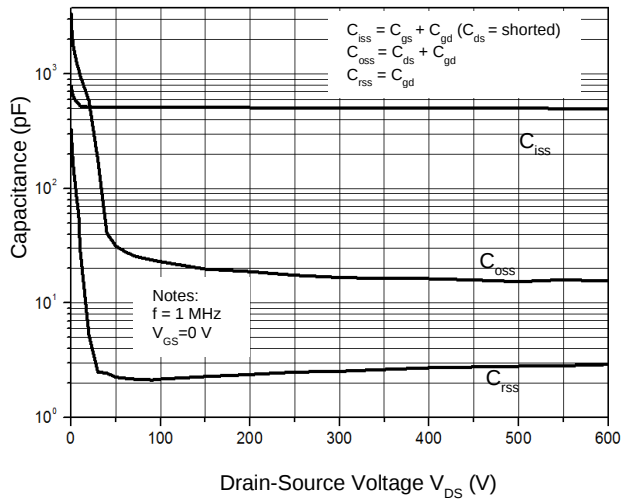


Figure 8. Gate Charge Characterist

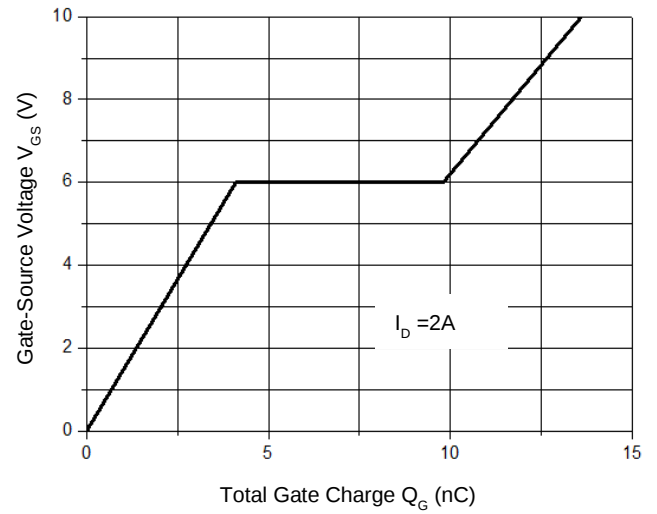


Figure 9.1 Maximum Safe Operating Area

TO-220MF

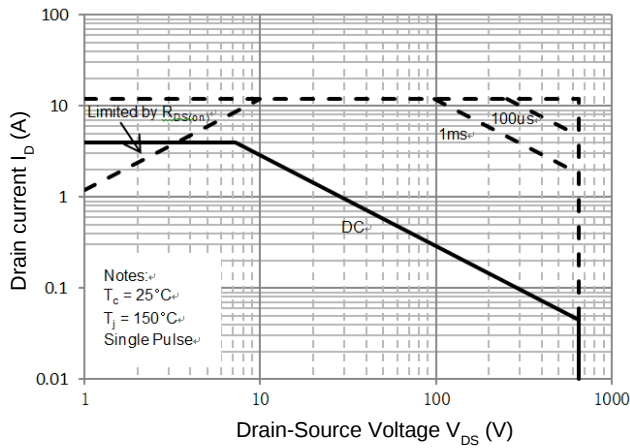


Figure 9.2 Maximum Safe Operating Area

TO-251/TO-252

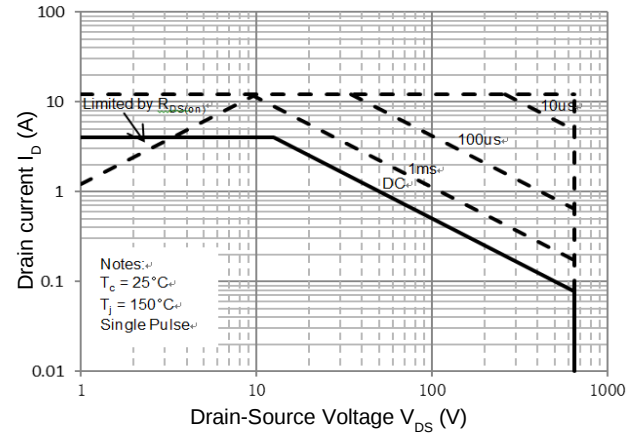


Figure 10.1 Power Dissipation vs. Temperature

TO-220MF

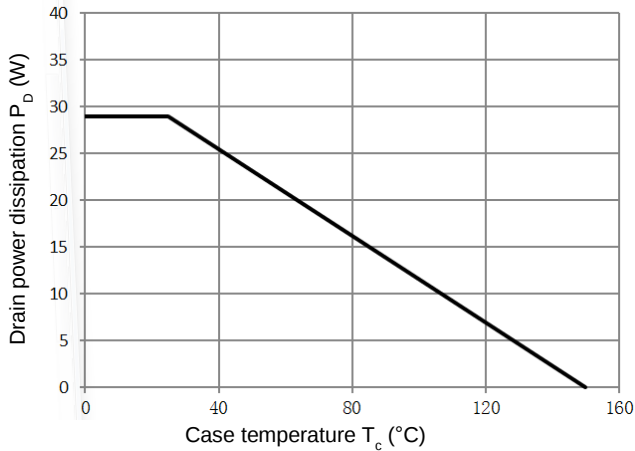


Figure 10.2 Power Dissipation vs. Temperature

TO-251/TO-252

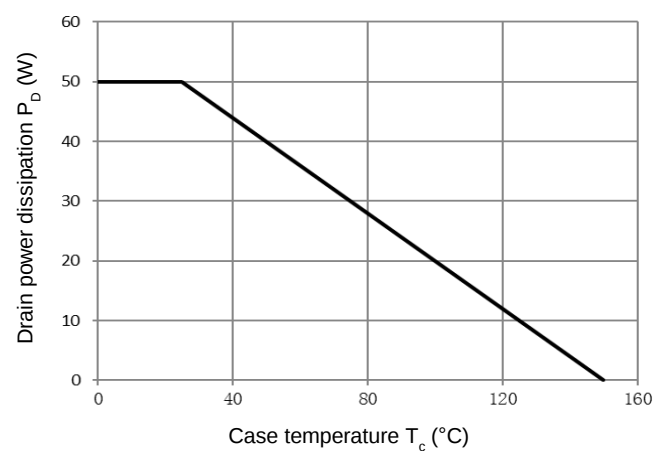


Figure 11.1 Transient Thermal Response Curve
TO-220MF

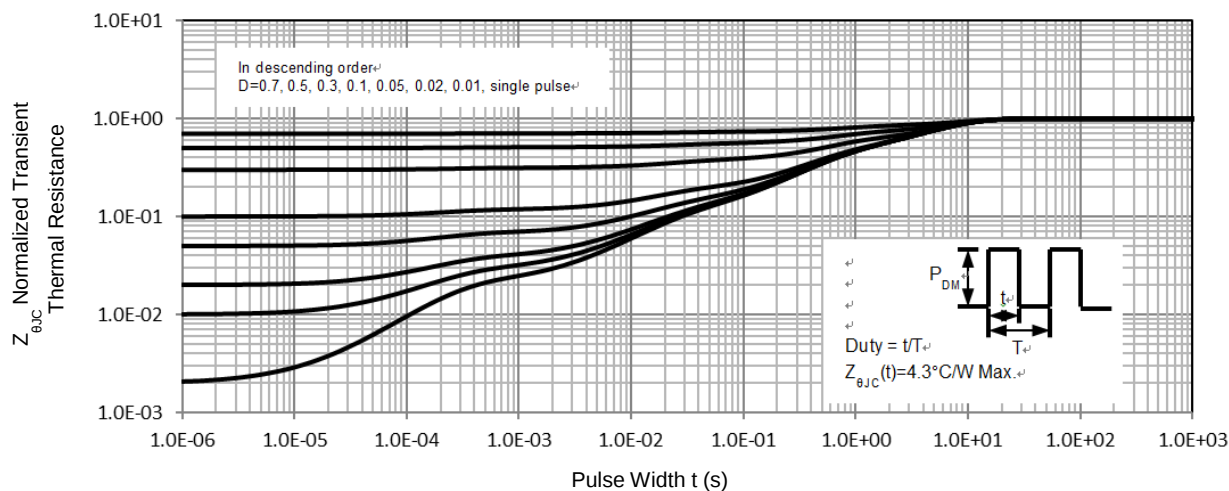
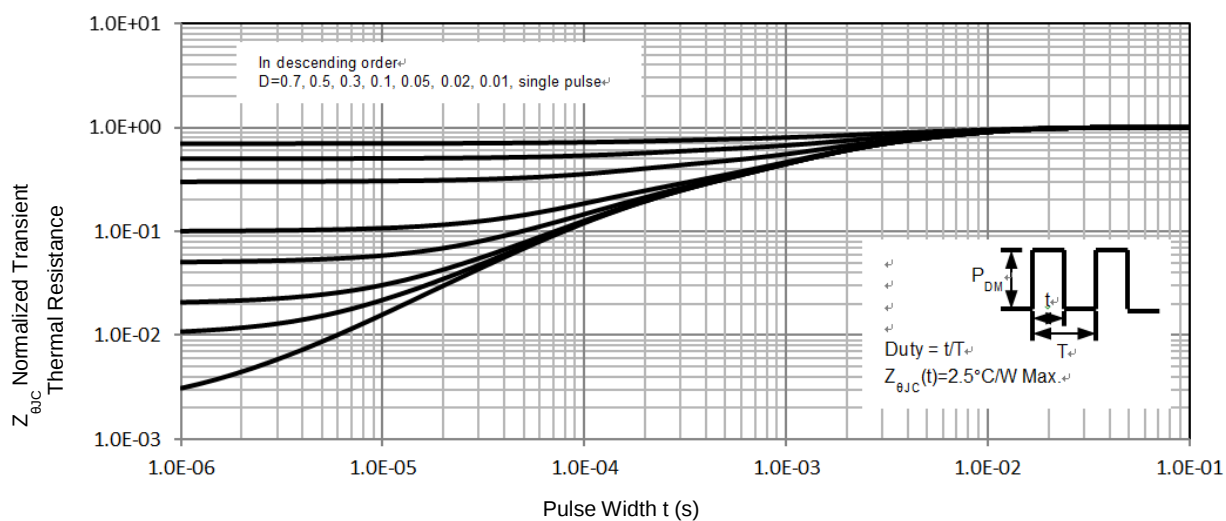
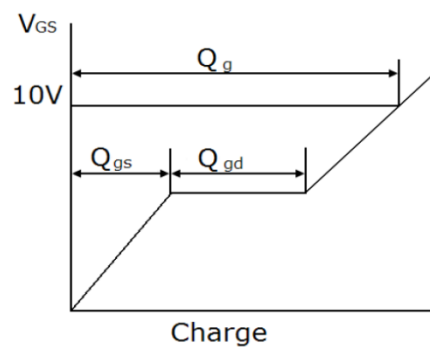
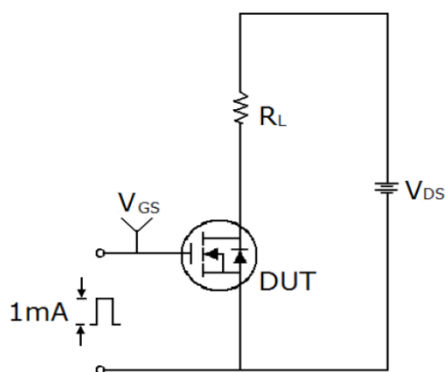


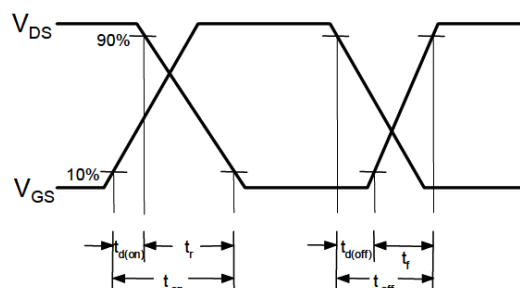
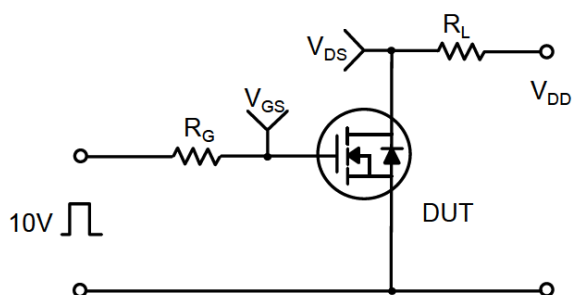
Figure 11.1 Transient Thermal Response Curve
TO-251/TO-252



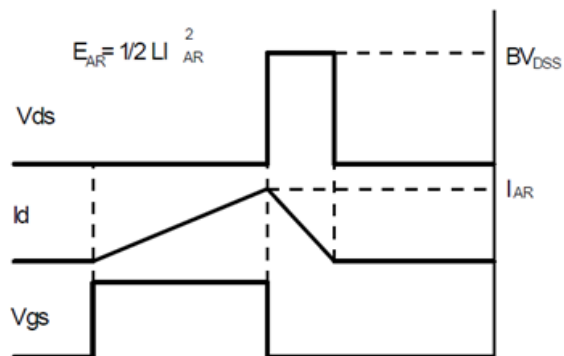
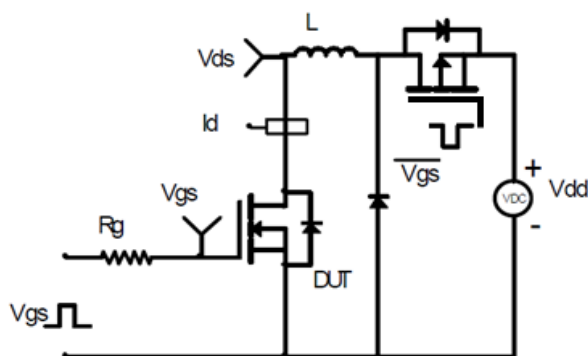
Gate Charge Test Circuit & Waveform



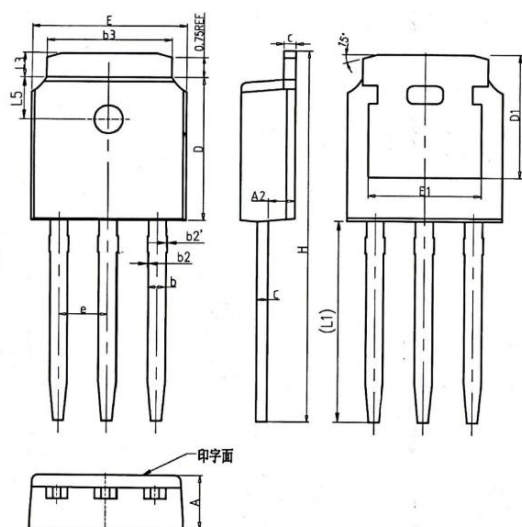
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

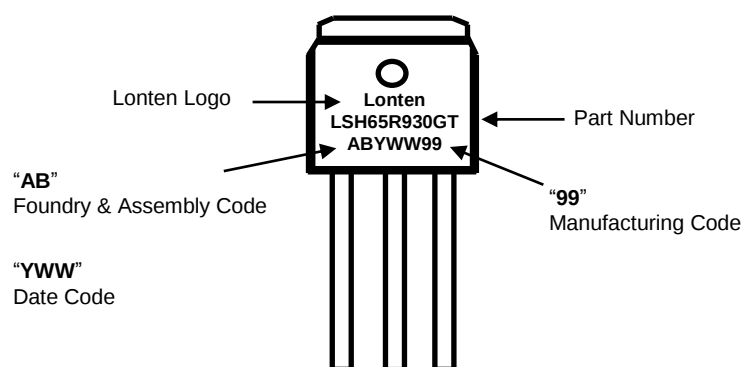


Mechanical Dimensions for TO-251

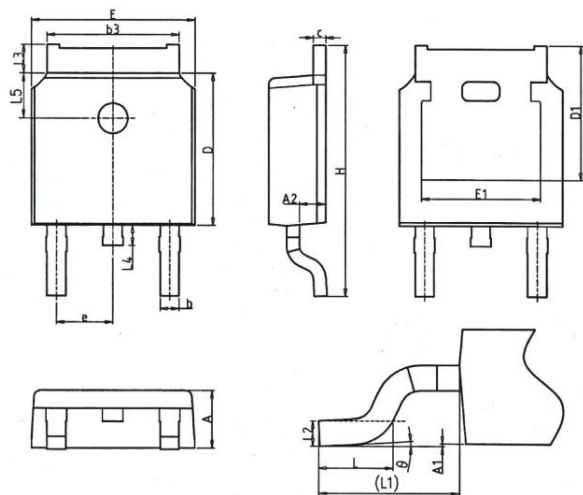


SYMBOL	COMMON DIMENSIONS		
	MM		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	—	—
e	2.286BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95

TO-251 Part Marking Information

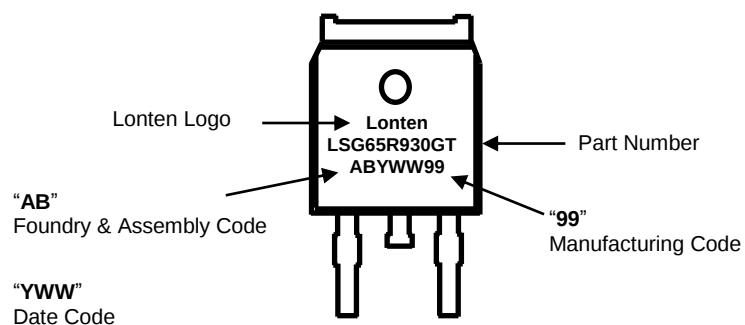


Mechanical Dimensions for TO-252

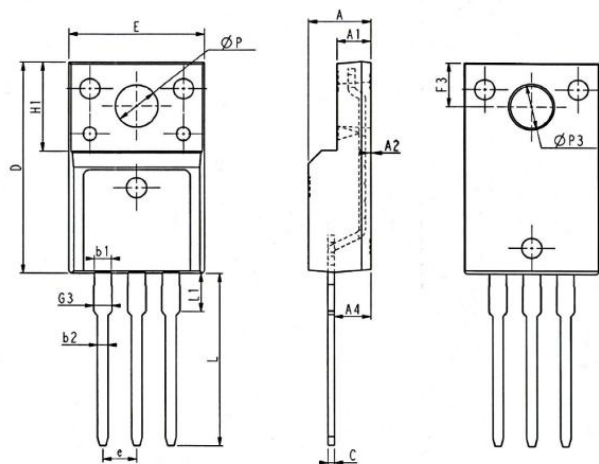


COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0.00	—	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	—	—
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	—	1.28
L4	0.50	—	1.00
L5	1.65	1.80	1.95
θ	0°	—	8°

TO-252 Part Marking Information

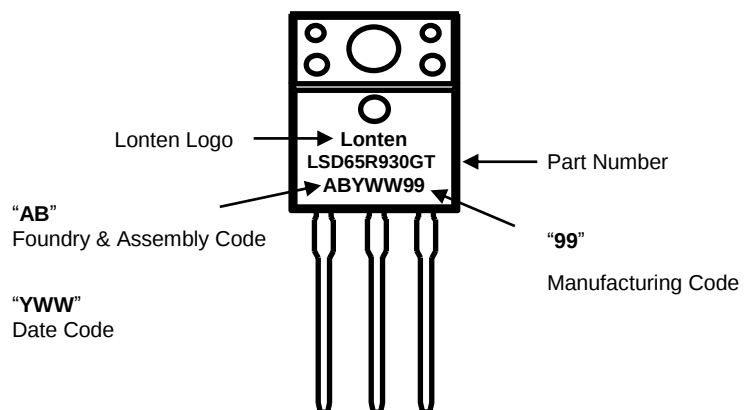


Mechanical Dimensions for TO-220MF



SYMBOL	COMMON DIMENSIONS					
	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
E	9.96	10.16	10.36	0.392	0.400	0.408
A	4.50	4.70	4.90	0.177	0.185	0.193
A1	2.34	2.54	2.74	0.092	0.100	0.108
A2	0.30	0.45	0.60	0.012	0.002	0.024
A4	2.65	2.76	2.96	0.104	0.109	0.117
C	0.40	0.50	0.65	0.016	0.020	0.026
D	15.57	15.87	16.17	0.613	0.625	0.637
H1	6.70REF			0.264REF		
e	2.54BSC			0.1BSC		
ØP	3.03	3.18	3.38	0.119	0.125	0.133
L	12.68	12.98	13.28	0.499	0.511	0.523
L1	2.88	3.03	3.18	0.113	0.119	0.125
ØP3	3.15REF			0.124REF		
F3	3.15	3.30	3.45	0.124	0.130	0.136
G3	1.25	1.35	1.55	0.049	0.053	0.061
b1	1.18	1.28	1.43	0.046	0.050	0.056
b2	0.70	0.80	0.95	0.028	0.031	0.037

TO-220MF Part Marking Information



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